

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,433,381 B2
APPLICATION NO. : 10/606104
DATED : October 7, 2008
INVENTOR(S) : Wang et al.

Page 1 of 2

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title Page

Item 56, References Cited, U.S. Patent Documents, replace “5,719,891 * 2/1998 Jewell
..... 372/46.013” with --5,719,891 * 2/1998 Jewell 372/45--

Item 56, References Cited, Other Publications, replace “Choquette et al., “High Single Mode
Operation from Hybrid Ion Implanted/Selectively Oxidezed VCSELs”, 2000 IEEE 17th International
Semiconductor Laser Conference, Monterrey, CA pp. 59-60.” with --Choquette et al., “High Single
Mode Operation from Hybrid Ion Implanted/Selectively Oxidezed VCSELs”, 200 IEEE 17th
International Semiconductor Laser Conference, Monterrey, CA pp. 59-60.--

Item 56, References Cited, Other Publications, replace “Morgan et al., Vertical-cavity surface
emitting lasers come of age, Invited paper, SPIE, vol. 2683 0-8194-2057, Mar. 1996, pp. 18-29.” with
--Morgan et al., “Vertical-cavity surface emitting lasers come of age”, Invited paper, SPIE, vol. 2683
0-8194-2057, Mar. 1996, pp. 18-29.--

Item 56, References Cited, Other Publications, replace “Smith, R.E. et al., Polarization-Sensitive
Subwavelength Antireflection Surfaces on a Semiconductor for 975 NM, *Optics Letters*, vol. 21, No.
15, Aug. 1, 1996, pp. 1201-1203.” with --Smith, R.E. et al., “Polarization-Sensitive Subwavelength
Antireflection Surfaces on a Semiconductor for 975 NM”, *Optics Letters*, vol. 21, No. 15, Aug. 1,
1996, pp. 1201-1203.--

Item 56, References Cited, Other Publications, replace “Tautm, et al., Commercialization of
Honeywell’s VCSEL Technology, Published in Proceedings fo the SPIE, vol. 3946, SPI, 2000, 12
pages.” with --Tautm, et al., “Commercialization of Honeywell’s VCSEL Technology”, Published in
Proceedings of the SPIE, vol. 3946, SPI, 2000, 12 pages.--

Item 56, References Cited, Other Publications, include the following omitted references:

--6,704,343 B2	03/2004	Deng et al.	372/97
6,810,056 B1	10/2004	Lipson et al.	372/46.01
6,829,281 B2	12/2004	Deng et al.	372/96
2004/0091010 A1	05/2004	Choquette et al.	372/044--

Column 2

Line 32, change “options” to --options,--

Line 34, change “InP based mirrors” to --InP-based mirrors--

Column 3

Line 33, change “upper mirror” to --upper mirror 19--

Line 35, change “trench” to --trench 23--

Line 42, change “structure 10” to --the VCSEL 10--

Line 56, change “structure 10” to --the VCSEL 10--

Line 59, change “structure 10” to --the VCSEL 10--

Line 66, change “of may be applied” to --or metal may be applied--

Column 4

Line 6, change "Top mirror 19" to --Top mirror 19,--
Line 6, change "cavity 17" to --cavity 17,--
Line 19, change "structure 10" to --the VCSEL 10--
Line 60, change "structure 10" to --the VCSEL 10--
Line 61, change "put into and oxidizing environment" to --put into an oxidizing environment,--

Column 5

Line 1, change "structure 10" to --the VCSEL 10--
Line 7, change "structure 10" to --the VCSEL 10--
Line 8, change "structure 10" to --the VCSEL 10--
Line 22, change "this view. But" to --this view, but--
Line 24, change "upper mirror" to --upper mirror 19--
Line 25, change "trench" to --trench 23--
Line 61, change "of may be applied" to --of metal may be applied--

Column 6

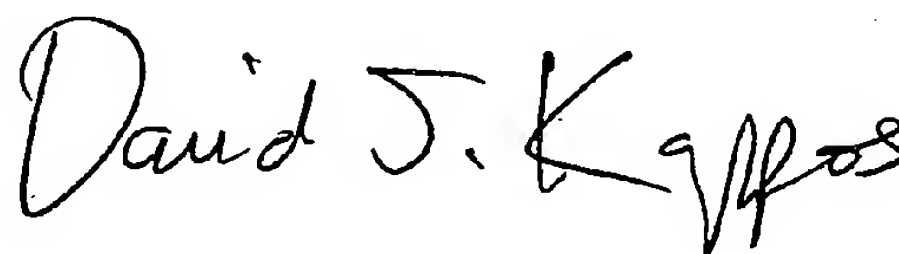
Line 59, change "InAlAs for example" to --InAlAs, for example,--
Line 60, change "into and" to --into an--
Line 61, change "environment" to --environment,--

Column 7

Line 8, change "structure 60 which" to --structure 60, which--

Signed and Sealed this

Twenty-third Day of February, 2010

A handwritten signature in black ink, reading "David J. Kappos". The signature is written in a cursive, flowing style with a large initial 'D' and 'K'.

David J. Kappos
Director of the United States Patent and Trademark Office